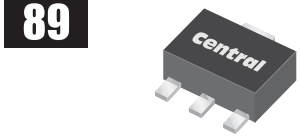
CXT7090L

SURFACE MOUNT
LOW $V_{CE(SAT)}$ PNP
SILICON POWER TRANSISTOR



SOT-89 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CXT7090L is a Low $V_{CE(SAT)}$ PNP Transistor in a Power SOT-89 surface mount package, designed for DC-DC converters for mobile systems and LAN cards, motor control, power management and strobe flash units.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	3.0	A
Peak Collector Current	I_{CM}	5.0	A
Power Dissipation	P_D	1.2	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	104	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C)

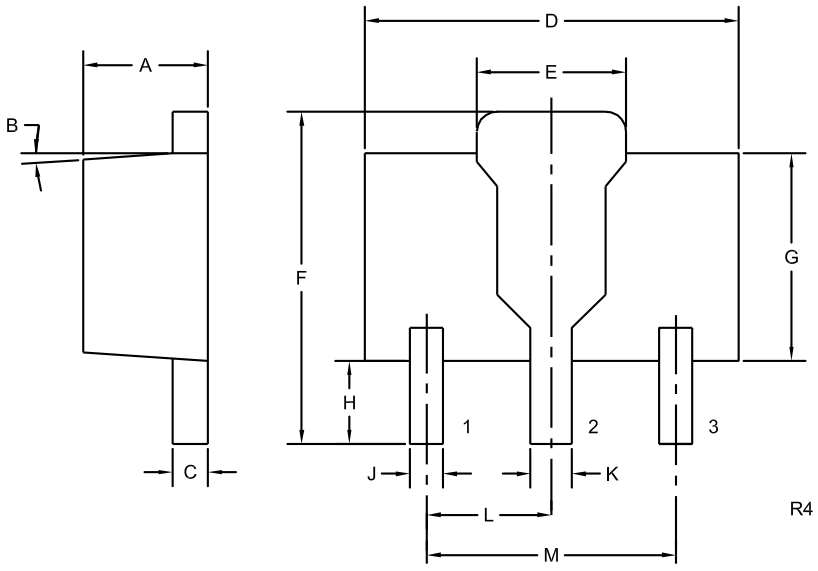
SYMBOL	**TEST CONDITIONS**	**MIN**	**TYP**	**MAX**	**UNITS**
I_{CBO}	V_{CB}=30V			100	nA
I_{CBO}	V_{CB}=30V, T_A=100°C			10	μA
I_{EBO}	V_{EB}=4.0V			100	nA
BV_{CBO}	I_C=100μA	50			V
BV_{CEO}	I_C=10mA	40			V
BV_{EBO}	I_E=100μA	5.0			V
$V_{CE(SAT)}$	I_C=500mA, I_B=5.0mA		100	250	mV
$V_{CE(SAT)}$	I_C=1.0A, I_B=10mA		175	450	mV
$V_{CE(SAT)}$	I_C=2.0A, I_B=50mA		250	750	mV
$V_{BE(SAT)}$	I_C=1.0A, I_B=10mA		0.8	1.0	V
h_{FE}	V_{CE}=2.0V, I_C=10mA	300		800	
h_{FE}	V_{CE}=2.0V, I_C=500mA	250			
h_{FE}	V_{CE}=2.0V, I_C=1.0A	200			
h_{FE}	V_{CE}=2.0V, I_C=2.0A	150			
f_T	V_{CE}=5V, I_C=50mA, f=50MHz	100			MHz

R3 (23-February 2010)

CXT7090L

SURFACE MOUNT
LOW $V_{CE(SAT)}$ PNP
SILICON POWER TRANSISTOR

SOT-89 CASE - MECHANICAL OUTLINE



(Bottom View)

LEAD CODE:
1) Emitter
2) Collector
3) Base

MARKING:
FULL PART NUMBER

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	4°		4°	
C	0.014	0.018	0.35	0.46
D	0.173	0.185	4.40	4.70
E	0.064	0.074	1.62	1.87
F	0.146	0.177	3.70	4.50
G	0.090	0.106	2.29	2.70
H	0.028	0.051	0.70	1.30
J	0.014	0.019	0.36	0.48
K	0.017	0.023	0.44	0.58
L	0.059		1.50	
M	0.118		3.00	

SOT-89 (REV: R4)

R3 (23-February 2010)